

STTH10R04

High efficiency rectifier

Features

- Ultrafast recovery
- Low power losses
- High surge capability
- Low leakage current
- High junction temperature

Description

The STTH10R04 is an ultrafast recovery power rectifier dedicated to energy recovery in PDP application.

It is especially designed for clamping function in energy recovery block.

The compromise between forward voltage drop and recovery time offers optimized performances.

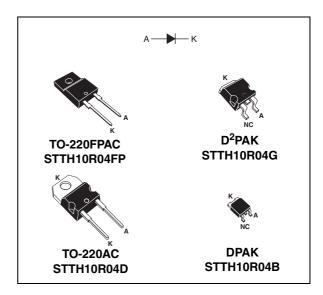


Table 1. Device summary

	=
I _{F(peak)}	10 A
V _{RRM}	400 V
t _{rr} (typ)	15 ns
T _j	175 °C
V _F (typ)	1.15 V

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Table 2. Absolute ratings (limiting values)

Symbol		Parameter			Unit
V _{RRM}	Repetitive peak reve	Repetitive peak reverse voltage			V
I _{F(RMS)}	Forward current (rms	Forward current (rms)			Α
	Peak working	DPAK, TO-220AC, D ² PAK	$T_c = 135 ^{\circ}\text{C} \delta = 0.5$ Square signal	10	А
'F(peak)	¹ F(peak) forward current	TO-220FPAC	$T_c = 130 ^{\circ}\text{C} \delta = 0.5$ Square signal	10	
I _{FSM}	Surge non-repetitive forward current $t_p = 10 \text{ ms sinusoidal}$		100	Α	
T _{stg}	Storage temperature range			-65 to + 175	°C
T _j	Maximum operating	junction temperature		175	°C

Table 3. Thermal parameters

Symbol	Parameter		Value	Unit
В		DPAK, TO-220AC, D ² PAK	3.5	°C/W
R _{th(j-c)}	Junction to case	TO-220FPAC	6	C/VV

Table 4. Static electrical characteristics

Symbol	Parameter	Test conditions		Min	Тур	Max	Unit
I _R ⁽¹⁾	Reverse leakage current	T _j = 25 °C	V - V			10	
I 'R`	$T_j = 125 ^{\circ}\text{C}$	$T_j = 125 ^{\circ}\text{C}$ $V_R = V_{RRI}$	10	100	μΑ		
V _E ⁽²⁾	Forward voltage drop	T _j = 25 °C	I _E = 10 A		1.5	1.7	V
VF \ /	Forward voltage drop	T _j = 125 °C	IF = IOA		1.15	1.35	v

^{1.} Pulse test: $t_p = 5 \text{ ms}, \delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 1.05 \text{ x } I_{F(AV)} + 0.03 I_{F^{2}(RMS)}$$

Table 5. Recovery characteristics

Symbol	Parameter	Test conditions			Тур	Max	Unit
+	Dayaraa raaayary tima T O		$I_F = 0.5 \text{ A}, I_{rr} = 0.25 \text{ A}, I_R = 1 \text{ A}$		15	20	ne
t _{rr}	Reverse recovery time	T _j = 25 °C	$I_F = 1 \text{ A}, V_R = 30 \text{ V}, dI_F/dt = -50 \text{ A/}\mu\text{s}$			40	ns
t _{fr}	Forward recovery time	T _j = 25 °C	$I_F = 10 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}$ $V_{FR} = 1.1 \text{ x } V_{Fmax}$			140	ns
V_{FP}	Peak forward voltage	T _j = 25 °C	$I_F = 10 \text{ A}$, $dI_F/dt = 100 \text{ A/}\mu\text{s}$			3	٧
I _{RM}	Reverse recovery current	T _ 125 °C	I _F = 10 A, V _{CC} = 200 V		6.2	8	Α
S _{factor}	Softness factor	1 _j = 125 C	$I_F = 10 \text{ A}, V_{CC} = 200 \text{ V}$ $dI_F/dt = 200 \text{ A}/\mu\text{s}$		0.3		

^{2.} Pulse test: t_p = 380 μ s, δ < 2%

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Figure 1. Conduction losses versus average forward current

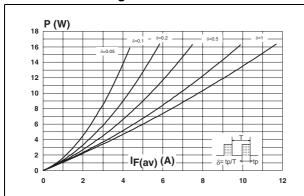


Figure 2. Forward voltage drop versus forward current

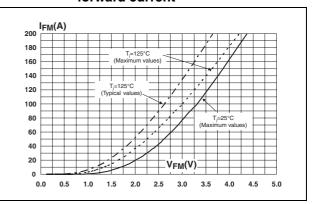


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

Z_{h(i,-}/R_{h(i,-c)}

1.0

0.9

Single pulse
DPAK

0.7

0.6

0.5

0.4

0.3

0.2

0.1

1.E-04

1.E-03

1.E-02

1.E-01

1.E+00

Figure 4. Relative variation of thermal impedance junction to case versus pulse duration

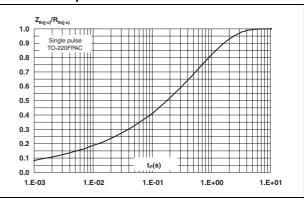


Figure 5. Peak reverse recovery current versus dl_F/dt (typical values)

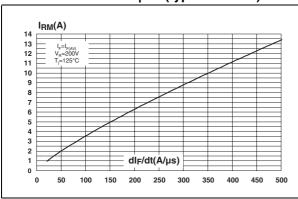
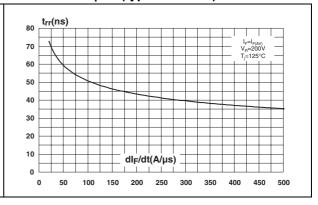


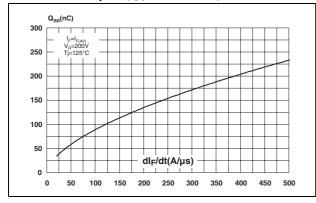
Figure 6. Reverse recovery time versus dl_F/dt (typical values)



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Figure 7. Reverse recovery charges versus dl_F/dt (typical values)

Figure 8. Reverse recovery softness factor versus dl_F/dt (typical values)



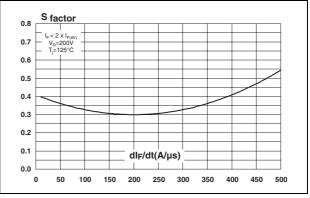
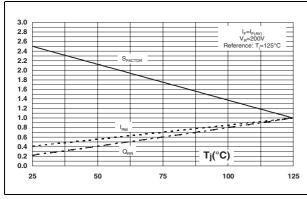
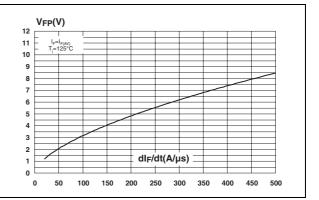


Figure 9. Relative variations of dynamic parameters versus junction temperature

Figure 10. Transient peak forward voltage versus dl_F/dt (typical values)





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Figure 11. Forward recovery time versus dl_F/dt (typical values)

Figure 12. Junction capacitance versus reverse voltage applied (typical values)

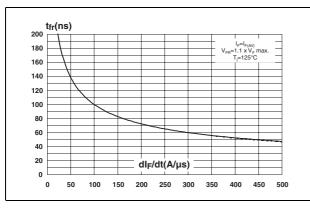
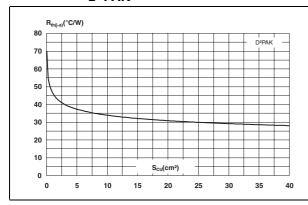
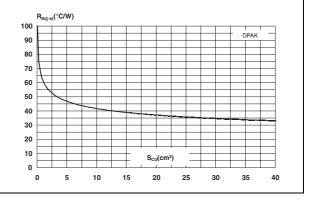


Figure 13. Thermal resistance, junction to ambient, versus copper surface under tab (epoxy printed board FR4, copper thickness = 35 μ m) D²PAK

Figure 14. Thermal resistance, junction to ambient, versus copper surface under tab (epoxy printed board FR4, copper thickness = 35 μm) DPAK





Package information STTH10R04

2 Package information

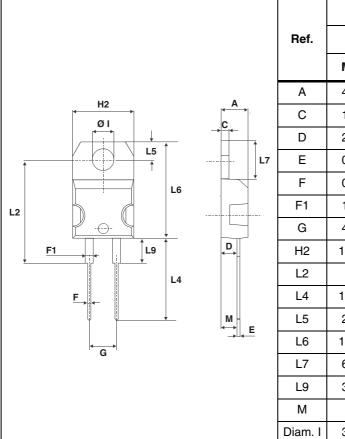
Epoxy meets UL94, V0

Cooling method: by conduction (C)Recommended torque calue: 0.8 N·m

Maximum torque value: 1.0 N⋅m

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.

Table 6. TO-220AC dimensions

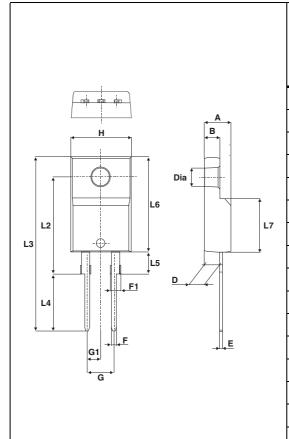


	Dimensions			
Ref.	Millimeters		Inc	hes
	Min.	Max.	Min.	Max.
Α	4.40	4.60	0.173	0.181
С	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
Е	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
H2	10.00	10.40	0.393	0.409
L2	16.40) typ.	typ. 0.645 typ.	
L4	13.00	14.00	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
М	2.6	typ.	0.102	2 typ.
Diam. I	3.75	3.85	0.147	0.151

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Table 7. TO-220FPAC dimensions

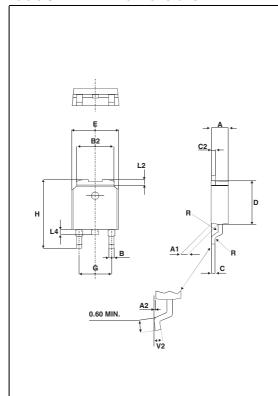


		Dimer	nsions	
Ref.	Millim	neters	Inc	hes
	Min.	Max.	Min.	Max.
Α	4.4	4.6	0.173	0.181
В	2.5	2.7	0.098	0.106
D	2.5	2.75	0.098	0.108
Е	0.45	0.70	0.018	0.027
F	0.75	1	0.030	0.039
F1	1.15	1.70	0.045	0.067
G	4.95	5.20	0.195	0.205
G1	2.4	2.7	0.094	0.106
Н	10	10.4	0.393	0.409
L2	16	Тур.	0.63 Typ.	
L3	28.6	30.6	1.126	1.205
L4	9.8	10.6	0.386	0.417
L5	2.9	3.6	0.114	0.142
L6	15.9	16.4	0.626	0.646
L7	9.00	9.30	0.354	0.366
Dia.	3.00	3.20	0.118	0.126

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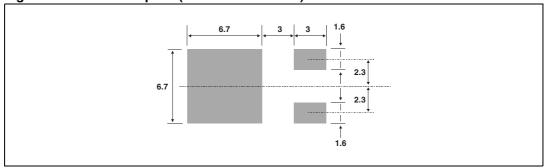
Package information STTH10R04

Table 8. DPAK dimensions



		Dimer	nsions		
Ref.	Millim	neters	Inches		
	Min.	Max.	Min.	Max.	
Α	2.20	2.40	0.086	0.094	
A1	0.90	1.10	0.035	0.043	
A2	0.03	0.23	0.001	0.009	
В	0.64	0.90	0.025	0.035	
B2	5.20	5.40	0.204	0.212	
С	0.45	0.60	0.017	0.023	
C2	0.48	0.60	0.018	0.023	
D	6.00	6.20	0.236	0.244	
Е	6.40	6.60	0.251	0.259	
G	4.40	4.60	0.173	0.181	
Н	9.35	10.10	0.368	0.397	
L2	0.80 typ.		0.03	1 typ.	
L4	0.60	1.00	0.023	0.039	
V2	0°	8°	0°	8°	

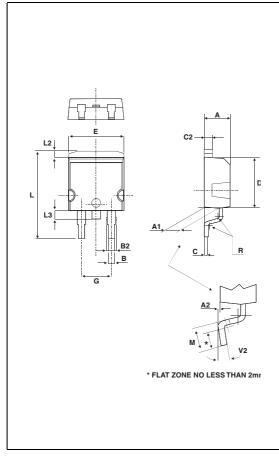
Figure 15. DPAK footprint (dimensions in mm)



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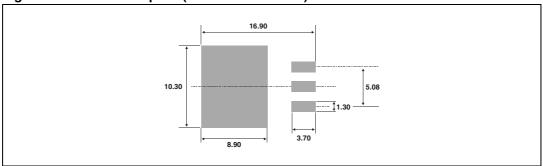
STTH10R04 Package information

Table 9. D²PAK dimensions



		Dimer	nsions	
Ref.	Millim	Millimeters		hes
	Min.	Max.	Min.	Max.
Α	4.40	4.60	0.173	0.181
A1	2.49	2.69	0.098	0.106
A2	0.03	0.23	0.001	0.009
В	0.70	0.93	0.027	0.037
B2	1.14	1.70	0.045	0.067
С	0.45	0.60	0.017	0.024
C2	1.23	1.36	0.048	0.054
D	8.95	9.35	0.352	0.368
Е	10.00	10.40	0.393	0.409
G	4.88	5.28	0.192	0.208
L	15.00	15.85	0.590	0.624
L2	1.27	1.40	0.050	0.055
L3	1.40	1.75	0.055	0.069
М	2.40	3.20	0.094	0.126
R	0.40	typ.	0.016	6 typ.
V2	0°	8°	0°	8°

Figure 16. D²PAK footprint (dimensions in mm)



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Ordering information STTH10R04

3 Ordering information

Table 10. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STTH10R04FP	STTH10R04FP	TO-220FPAC	1.64 g	50	Tube
STTH10R04B	STTH10R04B	DPAK	0.3g	75	Tube
STTH10R04B-TR	STTH10R04B	DEAR	0.3g	2500	Tape and reel
STTH10R04G	STTH10R04G	D ² PAK	1.48 g	50	Tube
STTH10R04G-TR	STTH10R04G	DIFAR	1.46 g	1000	Tape and reel
STTH10R04D	STTH10R04D	TO-220AC	1.86 g	50	Tube

4 Revision history

Table 11. Document revision history

Date	Revision	Description of changes
07-Nov-2007	1	First issue

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